

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

Listing of Claims:

Claim 1 (currently amended): A ~~copper alloy~~ sputtering target, ~~wherein comprising a~~ copper alloy sputtering target containing 0.5 to 4.0wt% of Al and 0.5wtppm or less of Si ~~are contained, and having an~~ average crystal grain size is of 0.1 to 60 $\mu$ m, and ~~the an~~ average grain size variation is of within  $\pm 20\%$ .

Claim 2 (currently amended): A copper alloy sputtering target according to claim 1, wherein said target further containing contains one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 1.0ppm or less.

Claim 3 (currently amended): A copper alloy sputtering target according to claim 1, wherein said target further containing contains one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 0.5ppm or less.

Claim 4 (currently amended): A ~~copper alloy~~ sputtering target, ~~wherein comprising a~~ copper alloy sputtering target containing 0.5 to 4.0wt% of Sn and 0.5wtppm or less of Mn ~~are contained, and having an~~ average crystal grain size is of 0.1 to 60 $\mu$ m, and ~~the an~~ average grain size variation is of within  $\pm 20\%$ .

Claim 5 (currently amended): A copper alloy sputtering target according to claim 4, wherein said target further ~~containing~~ contains one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 1.0ppm or less.

Claim 6 (currently amended): A copper alloy sputtering target according to claim 4, wherein said target further ~~containing~~ contains one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 0.5ppm or less.

Claims 7-14 (canceled).

Claim 15 (new): A copper alloy sputtering target according to claim 3, wherein a recrystallization temperature of said target is 365°C or less.

Claim 16 (new): A copper alloy sputtering target according to claim 15, wherein said target contains 1wtppm or less of oxygen.

Claim 17 (new): A copper alloy sputtering target according to claim 16, wherein said target contains 0.5 to 4.0wt% of Sn.

Claim 18 (new): A copper alloy sputtering target according to claim 1, wherein a recrystallization temperature of said target is 365°C or less.

Claim 19 (new): A copper alloy sputtering target according to claim 1, wherein said target contains 5wtppm or less of oxygen.

Claim 20 (new): A copper alloy sputtering target according to claim 1, wherein said target contains 0.5 to 4.0wt% of Sn.

Claim 21 (new): A copper alloy sputtering target according to claim 6, wherein said target contains 1wtppm or less of oxygen.

Claim 22 (new): A copper alloy sputtering target according to claim 21, wherein said target contains 0.5 to 4.0wt% of Al.

Claim 23 (new): A copper alloy sputtering target according to claim 4, wherein a recrystallization temperature of said target is 365°C or less.

Claim 24 (new): A copper alloy sputtering target according to claim 4, wherein said target contains 5wtppm or less of oxygen.

Claim 25 (new): A copper alloy sputtering target according to claim 4, wherein said target contains 0.5 to 4.0wt% of Al.

Claim 26 (new): Semiconductor element wiring prepared by a process comprising the step of forming the semiconductor element wiring from a copper alloy sputtering target containing 0.5 to 4.0wt% of Al or Sn and 0.5wtppm or less of Si or Mn and having an average crystal grain size of 0.1 to 60 $\mu$ m and an average grain size variation of within  $\pm 20\%$ .

Claim 27 (new): Semiconductor element wiring according to claim 26, wherein said semiconductor element wiring is a semiconductor wiring seed layer.

Claim 28 (new): Semiconductor element wiring according to claim 27, wherein said semiconductor wiring seed layer is formed on a barrier film of Ta, Ta alloy, or a nitride thereof.